

Attorney Docket No. 0756-2424

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Osamu NAKAMURA et al.
Serial No. 10/046,893
Filed: January 17, 2002
For: METHOD OF MANUFACTURING

SEMICONDUCTOR DEVICE

Group Art Unit: 2823

Examiner: H. Lee

CERTIFICATE OF MAILING

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Honorable Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The references cited on PTO 1449 Form, Page 1 (List 1), are all patents of the Assignee (Semiconductor Energy Laboratory Co., Ltd.), which may relate to the subject application.

The references cited on PTO 1449 Form, Pages 1-4 (List 2), are references which were cited in U.S. Serial No. 10/056,055. U.S. Serial No. 10/056,055 corresponds to U.S. Patent Publication No. 2002/0134981 (List 1)

A check in the amount of \$180 is being submitted to comply with the provisions of 37 C.F.R. § 1.97(c).

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be 11/04/2003 SSANDARA 00000006 10046893

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Respectfully submitted,

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Substitute for form 1449A/PTO				C	Complete if Known			
INFORMATION DISCLOSURE			TOSLIDE	Application Number	10/046,893	$\sim$	PER	
				Filing Date	January 17, 2002	70	4	
SIA	TEMENT BY			First Named Inventor	Osamu Nakamura et al.		3 1 2003 E	
	(use as many sheets	as neces.	sary)	Group Art Unit	2823	) OC	3 , 5	
				Examiner Name	H. Lee	\-0		
Sheet	1 (List 1)	of	1	Attorney Docket Number	0756-2424	*TON	& TRADEMARK	

				U.S. PATENT DOCU	MENTS				
Examiner Initials*	Cite No.1	U.S. Patent I	Kind Code <sup>2</sup> (If known)	Name of Patentee or Applicant of Document	Cited Date of Publication of Cite Document MM-DD-YYYY	d Pages, Columns, Lines, Wi Passages or Relevant Figu			
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				FOREIGN PATENT DO	CUMENTS				
Examiner Initials*	Cite No.1	Foreign Pater	nt Document	Name of Patentee or Applicant of Cited Documer	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T*		
	1	Office <sup>3</sup> Number	er <sup>4</sup> (if known,	)					
			OTHER PR	IOR ART – NON PATENT LI	TERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.							

Examiner	Date	
Signature	Considered	

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>&</sup>lt;sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

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Substitut	e for form 1449A/PTC	)		C	omplete if Known	100
INFO	INFORMATION DISCLOSURE		Application Number	10/046,893	PILE	
	TEMENT B			Filing Date	January 17, 2002	
SIA				First Named Inventor	Osamu Nakamura et al.	OCT 3 1 2003 W
	(use as many sheet	is as neces	sary)	Group Art Unit	2823	
				Examiner Name	H. Lee	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
Sheet	1 (List 2)	of	4	Attorney Docket Number	0756-2424	PADEMARK

Examiner		U.S. Patent Document	t	Date of Publication of Cited	Pages, Columns, Lines, Where Releva
Initials*	Cite No. <sup>1</sup>	Number Kind Code <sup>2</sup>	Name of Patentee or Applicant of Cited Document	Document MM-DD-YYYY	Passages or Relevant Figures Appear
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Substitute	for form 1449A/PTO		v	TRADEMA	Complete if Known
INFO	RMATION I	NECI	Aditso	Application Number	10/046,893
				Filing Date	January 17, 2002
STATEMENT BY APPLICANT				First Named Inventor	Osamu NAKAMURA et al.
	(use as many sheets o	is necessa	iry)	Group Art Unit	2823
_				Examiner Name	H. Lee
Sheet	2 (List 2)	of	4	Attorney Docket Number	0756-2424

	T	U.S. Patent Document	U.S. PATENT DOCUMEN'	Date of Publication of Cited	Pages, Columns, Lines, Where Releva
Examiner Initials	Cite No. <sup>1</sup>	Number Kind Code <sup>2</sup>	Name of Patentee or Applicant of Cited Document	Document MM-DD-YYYY	Passages or Relevant Figures Appear
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3 (List 2)

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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/046,893		
Filing Date	January 17, 2002		
First Named Inventor	Osamu NAKAMURA et al.		
Group Art Unit	2823		
Examiner Name	H. Lee		
Attorney Docket Number	0756-2424		

				U.S. PATENT DOCUMEN	rs	
Examiner Initials	Cite No.¹	U.S. Patent Docum	ent d Code <sup>2</sup>	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials'    Cite   Number'   Number'   Number'   Number'   Number   Number		,		FOREIGN PATENT DOC	UMENTS				
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JP 09-074207   03/18/1997    JP 3032801   12/18/2000    JP 2001/210828   08/03/2001    JP 2000/260777   09/22/2000    EP 0 651 431   05/03/1995    OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS  Examiner Initials   No.   Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.  Masayasu Miyake et al., Characteristics of Buried-Channel pMOS Devices with Shallow Counter-Doped Layers Fabricated Using Channel Preamorphization, IEEE Transactions on Electron Devices, Vol. 43, No. 3, March 1996, pp. 444-449  Lurng S. Lee et al., Argon Ion-Implantation on Polysilicon or Amorphous-Silicon for Boron Penetration Suppression in p+ pMOSFET, IEEE Transactions on Electron Devices, Vol. 45, No. 8, August 1998, pp. 1737-1744  Kevin S. Jones et al., Boron Diffusion Upon Annealing of Laser Thermal Processed Silicon, Ion Implantation Technology 2000, IEEE 2000, pp. 111-114  D.J. Llewellyn et al., Implantation and Annealing of CU in InP for Electrical Isolation: Microstructural Characterisation, Optoelectronic and Microelectronic Materials and		JP	07-183540		07/21/1995		AB		
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